

Serial No. To be assigned

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	GIORGI et al.	Examiner:	Unknown
Serial No.:	To be assigned	Group Art Unit:	Unknown
Filed:	July 1, 2003	Docket No.:	00970.0009-US-01
Title:	LIGHT ACTIVATED SEMICONDUCTOR SWITCHES		

CERTIFICATE UNDER 37 C.F.R. 1.10:

'Express Mail' mailing number: EV 314776764 US

Date of Deposit: July 1, 2003

The undersigned hereby certifies that this Transmittal Letter and the paper or fee, as described herein, are being deposited with the United States Postal Service 'Express Mail Post Office To Addressee' service under 37 CFR 1.10 and is addressed to the Commissioner for Patents, Alexandria, VA 22313-1450.

By: 

Bernadette Luhman

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97(b)

Mail Stop Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Applicant(s) respectfully submit(s) the items of information on the enclosed Form 1449 for the attention of the Examiner in the above-identified application.

This Information Disclosure Statement is being filed within three months of the filing of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d); within three months of the date of entry of the national stage as set forth in 37 C.F.R. 1.491 in an international application; before the mailing date of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 C.F.R. 1.114. Accordingly, no fee is due for consideration of the items listed on the enclosed Form 1449.

A copy of each document or other information listed on the enclosed Form 1449 is enclosed in accordance with 37 C.F.R. §1.98(a)(2) and/or a copy of each document is not provided because it was previously cited by or submitted to the U.S. Patent and Trademark Office in a parent application in accordance with 37 C.F.R. §.1.98(d).

No representation is made that a reference is "prior art" within the meaning of 35 U.S.C. §§102 and 103. In addition, Applicant(s) do(es) not represent that a reference has been thoroughly reviewed or that any relevance of any portion of a reference is intended, and reserve the right to establish otherwise under 37 C.F.R. §1.131 or others.

Consideration of the items listed is respectfully requested. According to M.P.E.P. §609, Applicant(s) request(s) that the Examiner return a copy of the attached Form 1449, marked as being considered and initialed by the Examiner, to the undersigned with the next official communication.

Authorization is hereby given to charge any additional fees or credit any overpayments that may be deemed necessary to Deposit Account Number 50-1038.

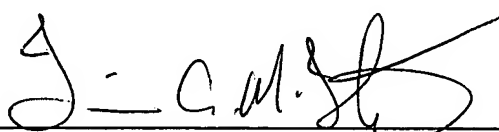
Respectfully submitted,

Altera Law Group, LLC



Date: July 1, 2003

By:


Iain A. McIntyre
Reg. No. 40,337
IAM/vlb

INFORMATION DISCLOSURE STATEMENT PTO Form 1449				Docket Number 00970.0009-US-01		Serial Number To be assigned		
				Applicant(s) GIORGI et al.				
				Filing Date July 1, 2003		Group Art Unit Unknown		
U.S. PATENT DOCUMENTS								
EXAMINER INITIALS	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE (IF APPROPRIATE)	
		3,590,344	06/29/71	Roberts et al.				
		4,186,409	01/29/80	McMullin				
		4,219,833	08/26/80	Temple				
		4,497,109	02/05/85	Huber et al.				
		4,572,947	02/28/86	Kao et al.				
		4,866,500	09/12/89	Nishizawa et al.				
		4,908,687	03/13/90	Temple				
		5,017,991	05/21/91	Nishizawa et al.				
		5,747,835	05/05/98	Pezzani				
		6,218,682	04/17/01	Zucker et al.				
FOREIGN PATENT DOCUMENTS								
EXAMINER INITIALS	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION	
							YES	NO
		DE 002738160	03/01/79	Germany			Abstract	
		JP 353112682	10/02/78	Japan			Abstract	
		JP 356152266	11/25/81	Japan			Abstract	
		JP 357196567	12/02/82	Japan			Abstract	
		JP 407015004A	01/17/95	Japan			Abstract	
OTHER DOCUMENTS								
		Alferov et al., "Electrically controllable three-electrode high-voltage subnanosecond switches made from a multilayer GaAs-AlGaAs heterostructure", <u>Sov. Tech Phys Lett.</u> November, 1986, American Institute of Physics, pp. 529-530.						
		Carson et al., "Long switching delay mechanisms for optically triggered GaAs thyristors", <u>Appl. Phys. Lett.</u> August 1991, American Institute of Physics, pp. 834-836.						
		Long et al., "New experiments with Light Activated Silicon Switches", <u>Appl. Phys. Lett.</u> December 27, 1977, pp. 1-3.						
		Page, "Some Advances in High Power, High di/dt, Semiconductor Switches", <u>Energy Storage, Compression and Switching</u> , 1976, pp. 415-421.						
		Zhao et al., "Dynamic I-V Characteristics of an AlGaAs/GaAs-Based Optothyristor for Pulsed Power-Switching Applications", <u>IEEE Electronic Device Letters</u> , Vol. 13, No. 3, March 1992, pp. 161-163.						
		Zhao et al., "Using Reverse Dynamic I-V Characteristics of AlGaAs/GaAs Optothyristor for Pulsed Power-Switching Applications", <u>Electronics Letters</u> , May 21, 1992, Vol. 28, No. 11, pp. 977-978.						
		Zucker et al., "Experimental demonstration of high-power fast-rise-time switching in silicon junction semiconductors", <u>Applied Physics Letters</u> , Vol. 29, No. 4, August 15, 1976, pp. 261-263.						
		"Proceedings: Light-Fired Thyristor Workshop", March 1978, Electric Power Research Institute, Palo Alto, California.						

Examiner:

Date Considered: